



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Hsiao, Tommy C.; Hui, Angela T.; Ogle, Robert B.; Pham, Tuan Duc;
Plat, Marina V.; Ramsbey, Mark T.; Shen, Lewis

Assignee: Advanced Micro Devices, Inc.

Title: Polished Flash Process With Metal Gates And Improved Planarity

Serial No.: 09/430,366 Filing Date: October 28, 1999

Examiner: J. Chen Group Art Unit: 2813

Docket No.: M-7523 US

San Jose, California
November 13, 2001

COMMISSIONER FOR PATENTS
Washington, D. C. 20231

AMENDMENT

Dear Sir:

This is a response to the August 15, 2001 Office Action. Submitted herewith is also a Summary of Telephonic Interview with Examiner, which memorializes the telephonic interview by Applicants' Attorney, J. Far-hadian, with Examiner Jack Chen on October 2001, pursuant to 37 CFR 1.133(b).

IN THE CLAIMS

The following is a clean version of the entire set of pending claims. In accordance with 37 CFR §1.121(c)(1)(ii), Attachment A provides marked up versions of the claims containing the newly introduced changes.

1. A method of making a flash memory cell including a substrate and a floating gate, the method comprising:

11/28/2001 EABURAK1 00000098 192386
01 FC:102 84.00 CH

LAW OFFICES OF
SKJERVEN MORRILL
MACPHERSON LLP

25 METRO DRIVE
SUITE 700
SAN JOSE, CA 95110
(408) 453-9200
FAX (408) 453-7779

RECEIVED
NOV 30 2001
TC 800 MAIL ROOM

C. J. Cat